ASSP

Single Serial Input PLL Frequency Synthesizer On-chip 1.2 GHz Prescaler

MB15E03SL

■ DESCRIPTION

The Fujitsu MB15E03SL is a serial input Phase Locked Loop (PLL) frequency synthesizer with a 1.2GHz prescaler. The prescaler has a selectable dual modulus division ratio of 64/65 or 128/129 enabling pulse swallow operation.

The MB15E03SL uses the latest Fujitsu BiCMOS process resulting in a typical supply current of 2.0mA at 2.7V. A refined charge pump design supplies a well balanced output current of 1.5mA or 6mA, and enhances phase and spurious noise performance. The charge pump current is selectable through serial data programming. The operating supply voltage range is between 2.4V and 3.6V supporting power sensitive applications.

MB15E03SL is ideally suited for wireless mobile communications including GSM, IS-136, IS-95 and ISM900 applications.

■ FEATURES

- High frequency operation: 1.2GHz max
- Low power supply voltage: Vcc = 2.4V to 3.6V
- Ultra Low power supply current: Icc = 2.0 mA typ. (Vcc = Vp = 2.7 V, $Ta = +25 ^{\circ}\text{C}$, in locked state)

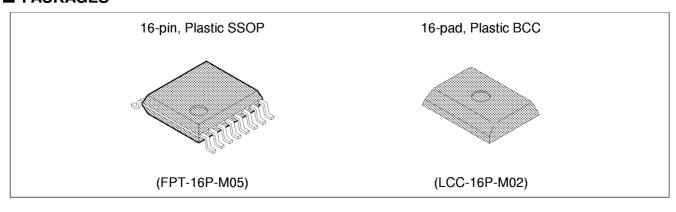
Icc = 2.5mA typ. (Vcc = Vp = 3V Ta = +25°C, in locked state)

• Direct power saving function: Power supply current in power saving mode

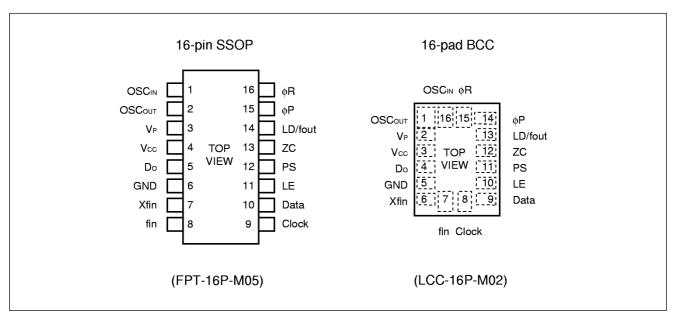
Typ. $0.1\mu A$ (Vcc = Vp = 3V, Ta = +25°C), Max. $10\mu A$ (Vcc = Vp = 3V)

- Dual modulus prescaler: 64/65 or 128/129
- Serial input 14-bit programmable reference divider: R = 3 to 16,383
- Serial input programmable divider consisting of:
 - Binary 7-bit swallow counter: 0 to 127
 - Binary 11-bit programmable counter: 3 to 2,047
- Selectable charge pump current (±1.5mA or ±6.0mA)
- On-chip phase control for phase comparator
- Operating temperature: Ta = -40 to +85°C
- Pin compatible with MB15E03, MB15E03L

■ PACKAGES



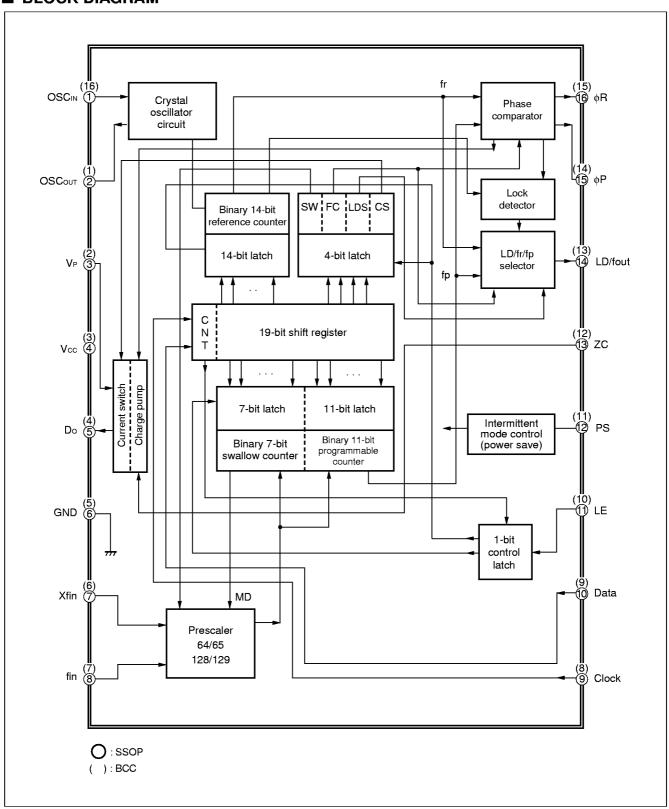
■ PIN ASSIGNMENTS



■ PIN DESCRIPTION

Pin	No.	Pin	1/0	Do covintion o
SSOP	всс	Name	I/O	Descriptions
1	16	OSCIN	I	Programmable reference divider input. Oscillator input connection to a TCXO.
2	1	OSCout	0	Oscillator output.
3	2	VP	_	Power supply voltage input for the charge pump.
4	3	Vcc	_	Power supply voltage input.
5	4	Do	0	Charge pump output. Phase of the charge pump can be selected via programming of the FC bit.
6	5	GND	_	Ground.
7	6	Xfin	I	Prescaler complementary input which should be grounded via a capacitor.
8	7	fin	I	Prescaler input. Connection to an external VCO should be done via AC coupling.
9	8	Clock	I	Clock input for the 19-bit shift register. Data is shifted into the shift register on the rising edge of the clock. (Open is prohibited.)
10	9	Data	I	Serial data input using binary code. The last bit of the data is a control bit. (Open is prohibited.)
11	10	LE	I	Load enable signal input. (Open is prohibited.) When LE is set high, the data in the shift register is transferred to a latch according to the control bit in the serial data.
12	11	PS	I	Power saving mode control. This pin must be set at "L" at Power-ON. (Open is prohibited.) PS = "H"; Normal mode PS = "L"; Power saving mode
13	12	ZC	I	Forced high-impedance control for the charge pump (with internal pull up resistor.) ZC = "H"; Normal Do output. ZC = "L"; Do becomes high impedance.
14	13	LD/fout	0	Lock detect signal output (LD)/phase comparator monitoring output (fout). The output signal is selected via programming of the LDS bit. LDS = "H"; outputs fout (fr/fp monitoring output) LDS = "L"; outputs LD ("H" = locked state, "L" = unlocked state)
15	14	φР	0	Phase comparator N-channel open drain output for an external charge pump. Phase can be selected via programming of the FC bit.
16	15	φR	0	Phase comparator CMOS output for an external charge pump. Phase can be selected via programming of the FC bit.

■ BLOCK DIAGRAM



■ ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Rat	ting	Unit	Remark	
Farameter	Symbol	Min.	Max.	Oille		
Power supply voltage	Vcc	-0.5	4.0	V		
Fower supply voltage	VP	Vcc	6.0	V		
Input voltage	Vı	-0.5	Vcc +0.5	V		
Output voltage	Vo	GND	V P	V		
Storage temperature	Tstg	- 55	+125	°C		

WARNING: Semiconductor devices can be permanently damaged by application of stress (voltage, current, temperature, etc.) in excess of absolute maximum ratings. Do not exceed these ratings.

■ RECOMMENDED OPERATING CONDITIONS

Parameter	Symbol		Value	Unit	Remark	
Farameter	Symbol	Min.	Тур.	Max.	Onit	nemark
Power cumply voltage	Vcc	2.4	3.0	3.6	V	
Power supply voltage	V P	Vcc	_	5.5	V	
Input voltage	Vı	GND	_	Vcc	٧	
Operating temperature	Та	-40	_	+85	°C	

WARNING: The recommended operating conditions are required in order to ensure the normal operation of the semiconductor device. All of the device's electrical characteristics are warranted when the device is operated within these ranges.

Always use semiconductor devices within their recommended operating condition ranges. Operation outside these ranges may adversely affect reliability and could result in device failure.

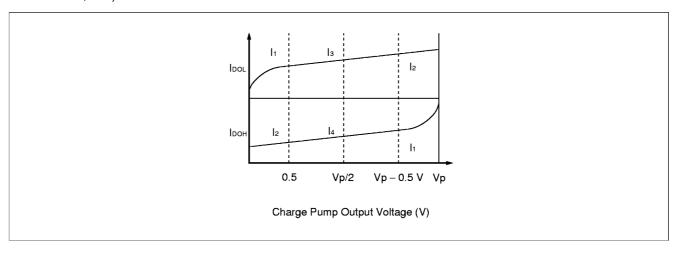
No warranty is made with respect to uses, operating conditions, or combinations not represented on the data sheet. Users considering application outside the listed conditions are advised to contact their FUJITSU representatives beforehand.

■ ELECTRICAL CHARACTERISTICS

 $(Vcc = 2.4 \text{ to } 3.6\text{V}, Ta = -40 \text{ to } +85^{\circ}\text{C})$

Davamatav		Coursels of	0			Value		I I an i A	
Parameter		Symbol	Con	dition	Min.	Тур.	Max.	Unit	
Power supply current*1		lcc*1	Vcc = VP = 2.7V (Vcc = VP = 3.0V	_	2.0 (2.5)	_	mA		
Power saving current		I PS	ZC = "H" or ope		0.1*2	10	μΑ		
Operating frequency	fin	fin	-		100	_	1200	MHz	
Operating frequency	OSCIN	OSCIN	-	_	3	_	40	MHz	
Input sensitivity	fin⁺³	Pfin	50Ω system (Refer to Measu	urement circuit)	-15	_	+2	dBm	
,	OSC _{IN*3}	Vosc	-		0.5	_	Vcc	Vp-p	
"H" level input voltage	Data,	Vн	-	_	$Vcc \times 0.7$	_	_		
"L" level input voltage	Clock, LE, PS, ZC	VIL	-	_	_	_	Vcc × 0.3	V	
"H" level input current	Data,	I 1H ^{*4}	-	<u> </u>	-1.0	_	+1.0		
"L" level input current	Clock, LE, PS	I _{IL} *4	-	_	-1.0	_	+1.0	μΑ	
"H" level input current		Iн	-	_	0	_	+100		
"L" level input current	OSCIN	I ı∟*4	-	-100	_	0	μA		
"H" level input current	70	I _{IH} *4	-	_		_	+1.0		
"L" level input current	ZC	I _{IL} *4	Pull up input		-100	_	0	μΑ	
"L" level output voltage	φР	Vol	Open drain out	out	_	_	0.4	٧	
"H" level output voltage	φR,	Vон	Vcc = Vp = 3V, I	он = -1mA	Vcc - 0.4	_			
"L" level output voltage	LD/fout	Vol	Vcc = V P = $3V$, I	oL = 1mA	_	_	0.4	V	
"H" level output voltage	Do	V DOH	$V_{CC} = V_P = 3V, I$	рон = -0.5mA	V _P − 0.4	_	_	V	
"L" level output voltage	100	V DOL	$V_{CC} = V_P = 3V, I$	DOL = 0.5mA	_	_	0.4	\ \	
High impedance cutoff current	Do	loff	$V_{CC} = V_P = 3V,$ $V_{OFF} = 0.5V \text{ to } V_{CC}$	/p — 0.5V	_	_	2.5	nA	
"L" level output current	φР	lol	Open drain out	out	1.0	_	_	mA	
"H" level output current	φR,	Іон	-	_	_	_	-1.0	т Л	
"L" level output current	LD/fout	lol	-	_	1.0	_		mA	
"H" level output current		I=*4	V 0V	CS bit = "H"	_	-6.0	_		
n level output current	Do	IDOH*4	$V_{CC} = 3V,$ $V_{P} = 3V,$	CS bit = "L"	_	-1.5	_	m A	
"L" level output current	Do	Inc	VDO = VP/2 Ta = +25°C	CS bit = "H"	_	6.0	_	mA	
L level output current	current IDOL Ia = +25°C CS bit =		CS bit = "L"	_	1.5	_			
	IDOL/IDOH	I DOМТ ^{*5}	$V_{DD} = V_P/2$		_	3	_	%	
Charge pump current characteristics	vs V _{DO}	ldovd*6	$0.5V \le V_{DO} \le V_{P}$	- 0.5V	_	10		%	
	vs Ta	IDOTA*7	– 40°C ≤ Ta ≤ +	85°C	_	10	_	%	

- *1: Conditions; fin = 1200MHz, fosc = 12MHz, $Ta = +25^{\circ}C$, in locking state. *2: Vcc = VP = 3.0V, fosc = 12.8 MHz, $Ta = +25^{\circ}C$, in power saving mode
- *3: AC coupling. 1000pF capacitor is connected under the condition of min. operating frequency.
 *4: The symbol "—" (minus) means direction of current flow.
- *5: Vcc = VP = 3.0V, Ta = +25°C (|I3| |I4|) / [(|I3| + |I4|) /2] × 100(%)
- *6: Vcc = VP = 3.0V, $Ta = +25°C [(||I_2| ||I_1|)/2] / [(||I_1| + ||I_2|)/2] \times 100(\%)$ (Applied to each IDOL, IDOH)
- *7: $V_{CC} = V_P = 3.0 \text{ V}$, $V_{DO} = V_P/2$ ($||D_{O(+85^{\circ}C)} |D_{O(-40^{\circ}C)}|/2$) / ($||D_{O(+85^{\circ}C)} + |D_{O(-40^{\circ}C)}|/2$) × 100(%) (Applied to each IDOL, IDOH)



■ FUNCTIONAL DESCRIPTION

1. Pulse Swallow Function

The VCO output frequency can be calculated using the following equation:

 $fvco = [(M \times N) + A] \times fosc \div R \quad (A < N)$

fvco : Output frequency of external voltage controlled oscillator (VCO)
 N : Preset divide ratio of binary 11-bit programmable counter (3 to 2,047)
 A : Preset divide ratio of binary 7-bit swallow counter (0 ≤ A ≤ 127)

fosc : Output frequency of the reference frequency oscillator

R : Preset divide ratio of binary 14-bit programmable reference counter (3 to 16,383)

M : Preset divide ratio of the dual modulus prescaler (64 or 128)

2. Serial Data Input

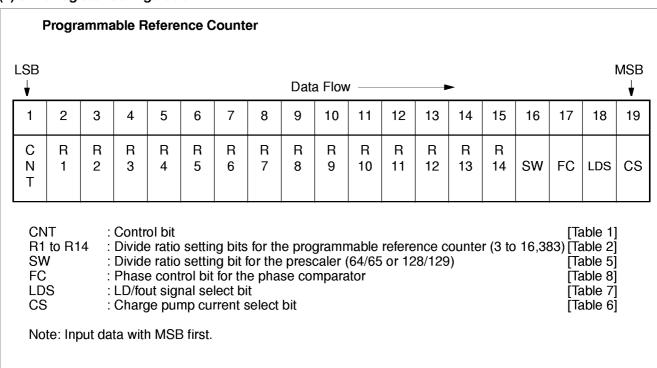
Serial data is entered using the Data, Clock, and LE pins. The serial data controls the programmable reference counter and the programmable counter separately.

Binary serial data is entered through the Data pin when the LE pin is held low. One bit of data is shifted into the shift register on the rising edge of the Clock. When the LE signal pin is taken high, entered data is latched into the appropriate counters according to the control bit setting as follows:

Table 1. Control Bit

Control Bit (CNT)	Destination of Serial Data
Н	For the programmable reference counter latch
L	For the programmable counter latch

(1) Shift Register Configuration



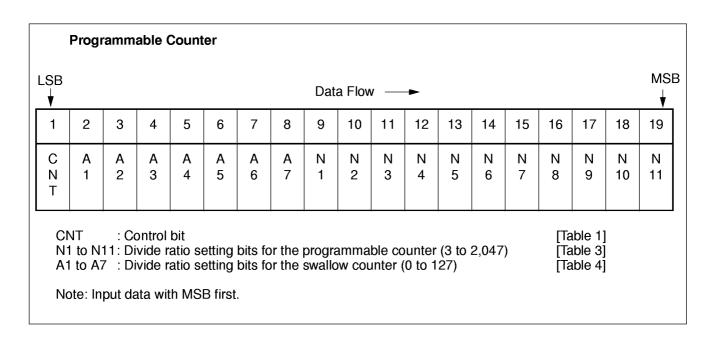


Table 2. Binary 14-bit Programmable Reference Counter Data Setting

Divide ratio (R)	R 14	R 13	R 12	R 11	R 10	R 9	R 8	R 7	R 6	R 5	R 4	R 3	R 2	R 1
3	0	0	0	0	0	0	0	0	0	0	0	0	1	1
4	0	0	0	0	0	0	0	0	0	0	0	1	0	0
16383	1	1	1	1	1	1	1	1	1	1	1	1	1	1

Note: • Divide ratio less than 3 is prohibited.

Table 3. Binary 11-bit Programmable Counter Data Setting

Divide ratio (N)	N 11	N 10	N 9	N 8	N 7	N 6	N 5	N 4	N 3	N 2	N 1
3	0	0	0	0	0	0	0	0	0	1	1
4	0	0	0	0	0	0	0	0	1	0	0
				٠	•			•	•		
2047	1	1	1	1	1	1	1	1	1	1	1

Note: • Divide ratio less than 3 is prohibited.

Table 4. Binary 7-bit Swallow Counter Data Setting

Divide ratio (A)	A 7	A 6	A 5	A 4	A 3	A 2	A 1
0	0	0	0	0	0	0	0
1	0	0	0	0	0	0	1
	•				•		
127	1	1	1	1	1	1	1

Table 5. Prescaler Data Setting

sw	Prescaler Divide Ratio
Н	64/65
L	128/129

Table 6. Charge Pump Current Setting

CS	Current Value
Н	±6.0mA
L	±1.5mA

Table 7. LD/fout Output Select Data Setting

LDS	LD/fouт Output Signal					
Н	fout signal					
L	LD signal					

(2) Relation between the FC Input and Phase Characteristics

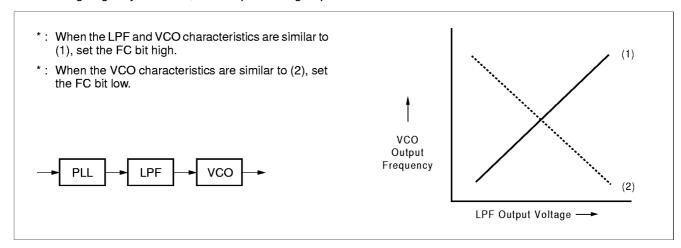
The FC bit changes the phase characteristics of the phase comparator. Both the internal charge pump output level (Do) and the phase comparator output (ϕ R, ϕ P) are reversed according to the FC bit setting. Also, the monitor pin (fout) output is controlled by the FC bit. The relationship between the FC bit setting and each of Do, ϕ R, and ϕ P is shown below.

Table 8. FC Bit Data Setting (LDS = "H")

		FC =	High		FC = Low					
	Dо	φR	φР	LD/fout	Do	φR	φР	LD/fout		
fr > f⊦	Н	L	L		L	Н	Z*			
fr < f⊳	L	Н	Z*	fout = fr	Н	L	L	fout = fp		
fr = f₽	Z*	L	Z*		Z*	L	Z*			

^{*:} High impedance

When designing a synthesizer, the FC pin setting depends on the VCO and LPF characteristics.



3. Do Output Control

Table 9. ZC Pin Setting

ZC pin	Do output	
Н	Normal output	
L	High impedance	

4. Power Saving Mode (Intermittent Mode Control Circuit)

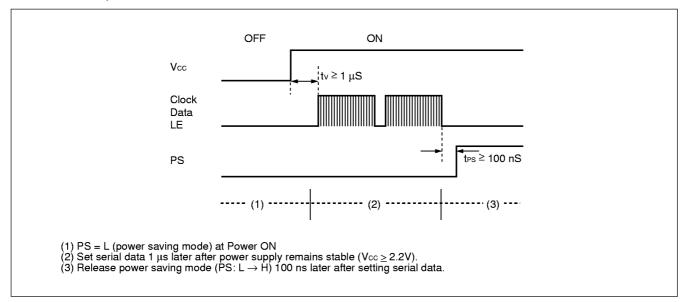
Table 10. PS Pin Setting

PS pin	Status	
Н	Normal mode	
L	Power saving mode	

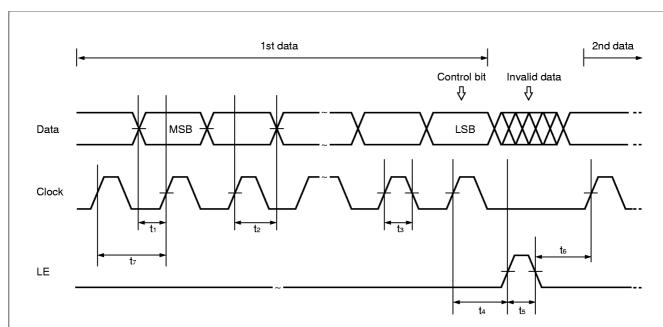
- The intermittent mode control circuit reduces the PLL power consumption. By setting the PS pin low, the device enters into the power saving mode. See the Electrical Characteristics chart for the specific value.
- The phase detector output, Do, becomes high impedance.
- · The lock detector ouput, LD, remains high.
- Setting the PS pin high releases the power saving mode, returing the device to normal operation.
- The intermittent mode control circuit also ensures a smooth startup when the device returns to normal operation.
 When the PLL is returned to normal operation, the phase comparator output signal is unpredictable. This is
 because of the unknown relationship between the comparison frequency (fp) and the reference frequency (fr)
 which can cause a major change in the comparator output, resulting in a VCO frequency jump and an increase
 in lockup time.
- To prevent a major VCO frequency jump, the intermittent mode control circuit limits the magnitude of the error signal from the phase detector when it returns to normal operation.

Note: When power (V_{CC}) is first applied, the device must be in standby mode, PS = Low, for at least 1 μ s.

Note: • PS pin must be set "L" for Power-ON.



■ SERIAL DATA INPUT TIMING



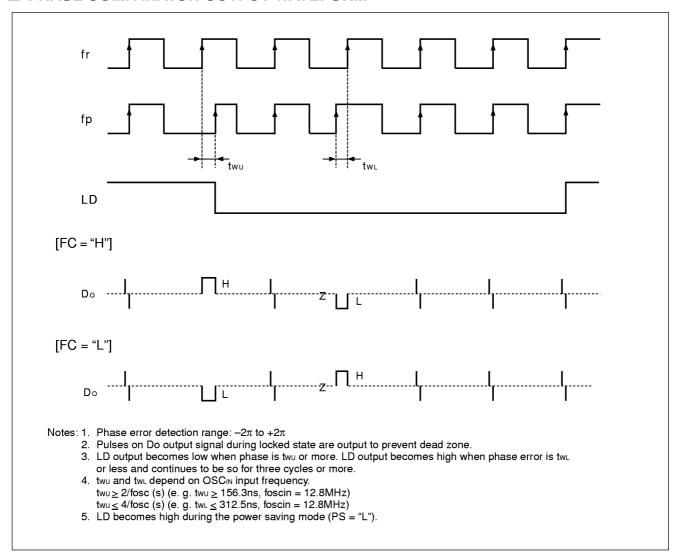
On the rising edge of the clock, one bit of data is transferred into the shift register.

Parameter	Min.	Тур.	Max.	Unit
t1	20	_	_	ns
t2	20	_	_	ns
t3	30	_	_	ns
t4	30	_	_	ns

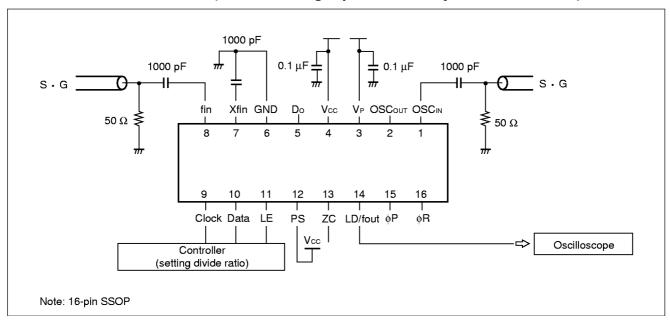
Parameter	Min.	Тур.	Max.	Unit
t5	100	_		ns
t6	20	_	_	ns
t7	100		_	ns

Note: LE should be "L" when the data is transferred into the shift register.

■ PHASE COMPARATOR OUTPUT WAVEFORM

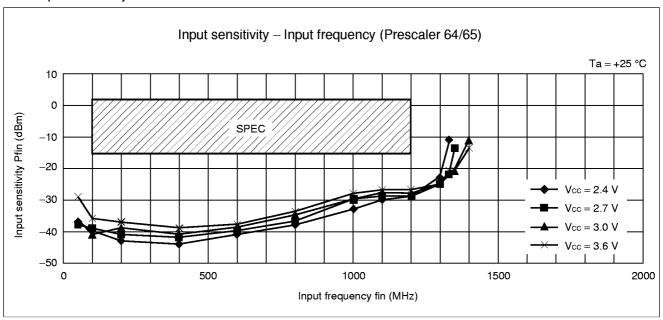


■ MEASURMENT CIRCUIT (for Measuring Input Sensitivity of fin and OSC_{IN})

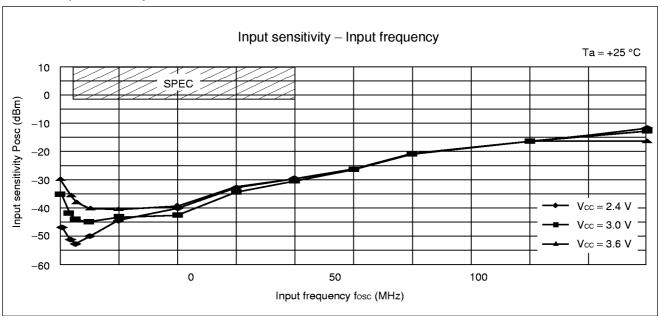


■ TYPICAL CHARACTERISTICS

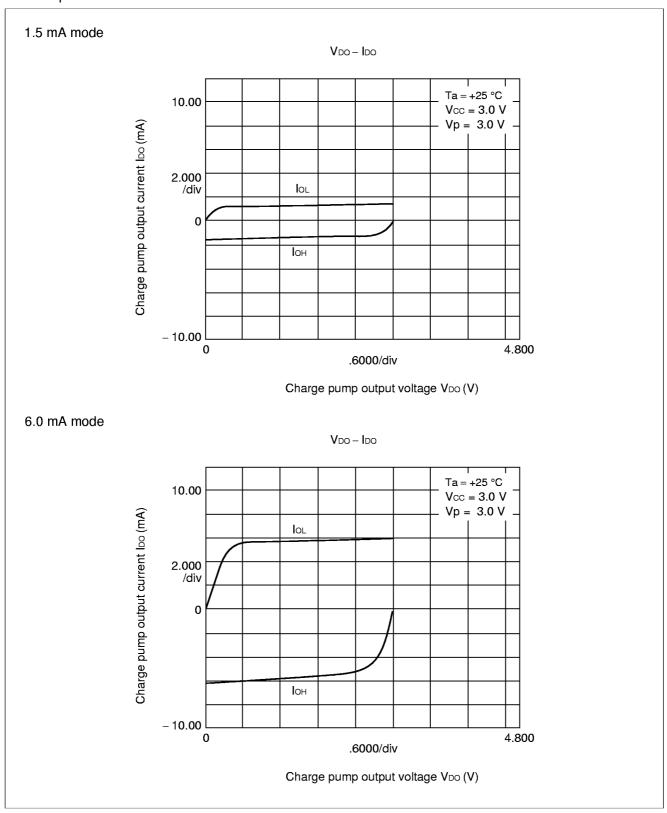
1. fin input sensitivity



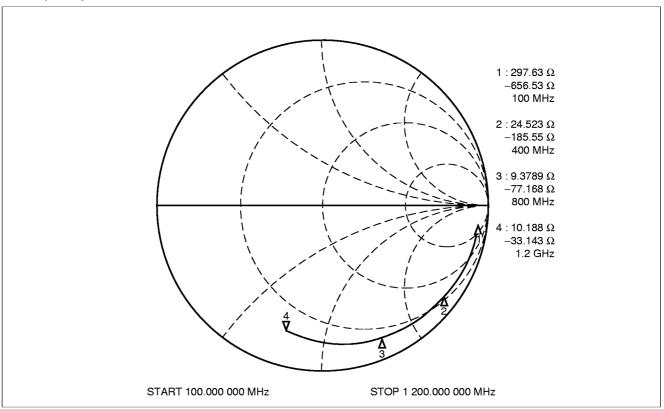
2. OSC_{IN} input sensitivity



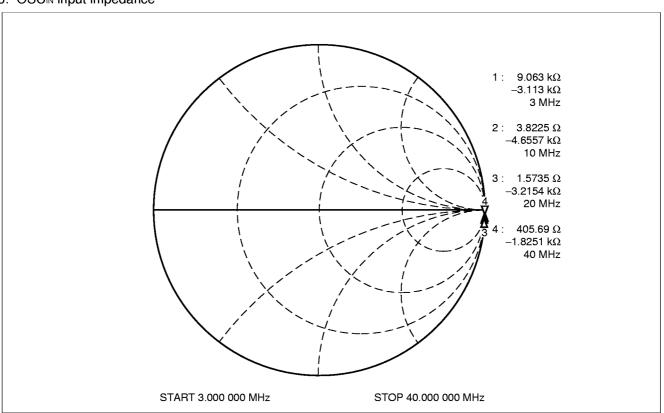
3. Do output current



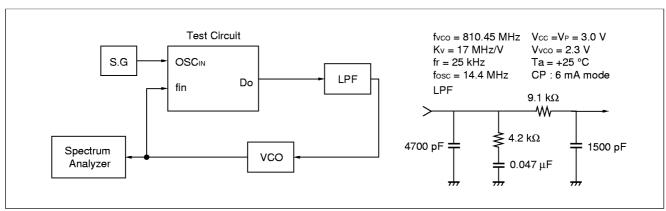
4. fin input impedance



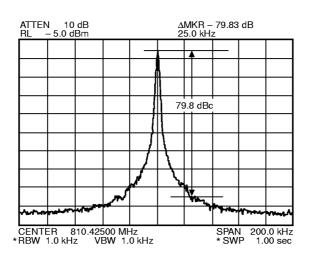
5. OSC_{IN} input impedance



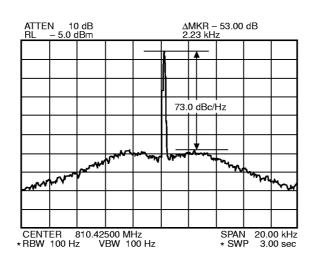
■ REFERENCE INFORMATION



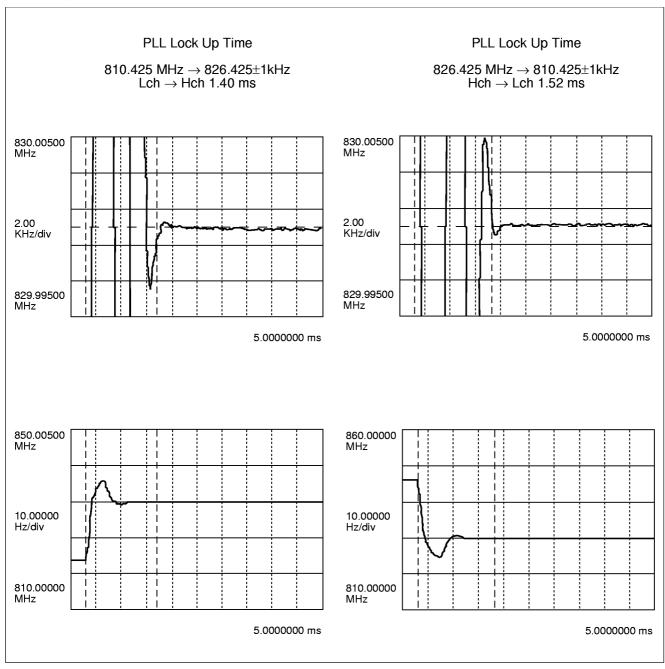
• PLL Reference Leakage



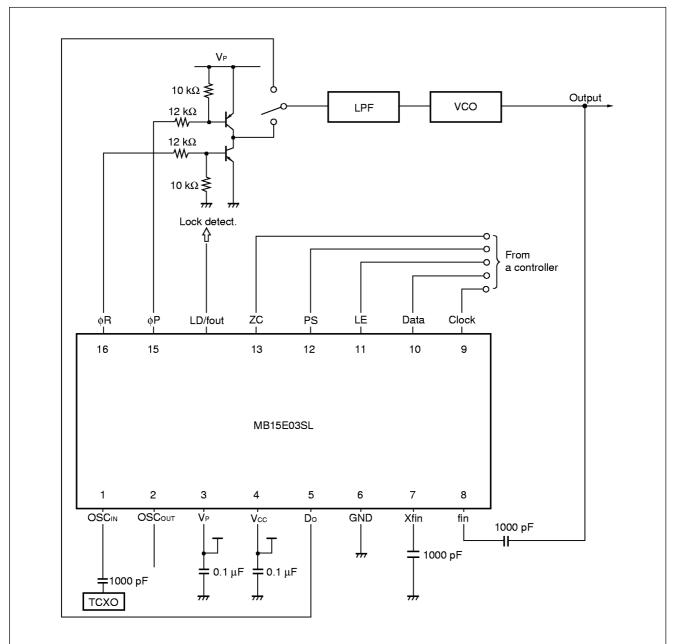
· PLL Phase Noise



(Continued)



■ APPLICATION EXAMPLE



Vp: 5.5 V Max

Notes: 1) 16-pin SSOP

2) In case of using a crystal resonator, it is necessary to optimize matching between the crystal and this device and it is advised to perform a detailed system evaluation. It is also recommended to consult with the supplier of the crystal resonator. (The reference oscillator circuit provides its own bias and the feedback resistor is 100 kΩ (typ).)

■ USAGE PRECAUTIONS

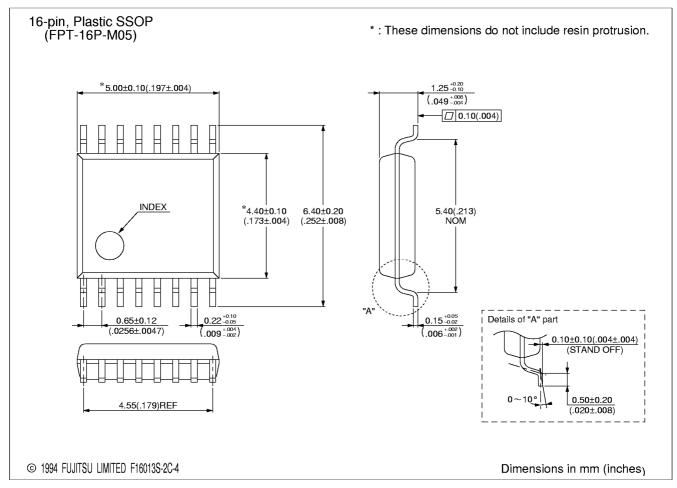
To protect against damage by electrostatic discharge, note the following handling precautions:

- Store and transport devices in conductive containers.
- Use properly grounded workstations, tools, and equipment
- Turn off power before inserting device into or removing device from a socket.
- Protect leads with a conductive sheet when transporting a board-mounted device.

■ ORDERING INFORMATION

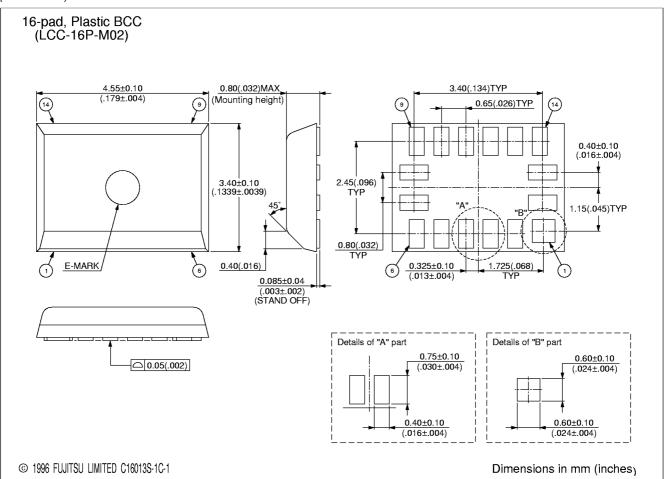
Part number	Package	Remarks
MB15E03SLPFV1	16-pin, Plastic SSOP (FPT-16P-M05)	
MB15E03SLPV	16-pad, Plastic BCC (LCC-16P-M02)	

■ PACKAGE DIMENSIONS



(Continued)

(Continued)



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